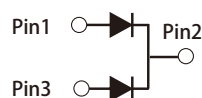
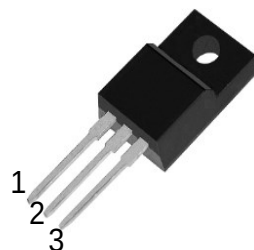


Features:

- ☐ Low power loss,high efficiency.
High surge capacity
- ☐ For use in low voltage,high frequency inverters,
free wheeling,and polarity protection applications.
- ☐ Metal silicon junction,majority carrier conduction.
- ☐ High current Capability,low forward voltage drop.
- ☐ Guard ring for over voltage protection.

TO-220F



1.Anode 2.Cathode 3. Anode

Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

PARAMETER		Symbol	MBRF 2040	MBRF 2045	MBRF 2050	MBRF 2060	MBRF 2080	MBRF 2090	MBRF 20100	MBRF 20150	MBRF 20200	Unit
Maximum Recurrent Peak Reverse Voltage		V _{RRM}	40	45	50	60	80	90	100	150	200	V
Maximum RMS Voltage		V _{RMS}	28	31.5	35	42	56	63	70	105	140	V
Maximum DC Blocking Voltage		V _{R(DC)}	40	45	50	60	80	90	100	150	200	V
Maximum Average Forward Current		I _{F(AV)}	20									A
Peak Forward Surge Current:8.3ms single half sine-wave superimposed on rated load (JEDEC method)		I _{FSM}	175									A
Maximum Forward Voltage at 10A per leg		V _F	0.65		0.72		0.85			0.95		V
Maximum DC Reverse Current at Rated DC Blocking Voltage	T _j =25℃	I _R	0.1									mA
	T _j =125℃		20									mA
Maximum Operating Junction Temperature		T _j	150				175				℃	
Storage Temperature		T _{stg}	-55~+ 150				-65~+175				℃	
Typical Thermal Resistance		R _{θJC}	1.4									℃/W

Typical Characteristics

RATING AND CHARACTERISTIC CURVES

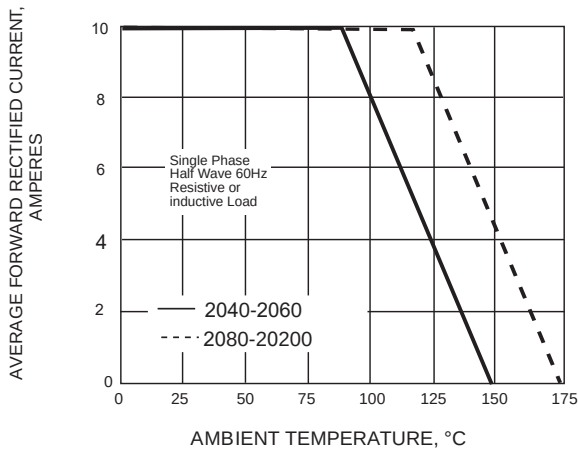


Fig.1 FORWARD CURRENT ERATING CURVE

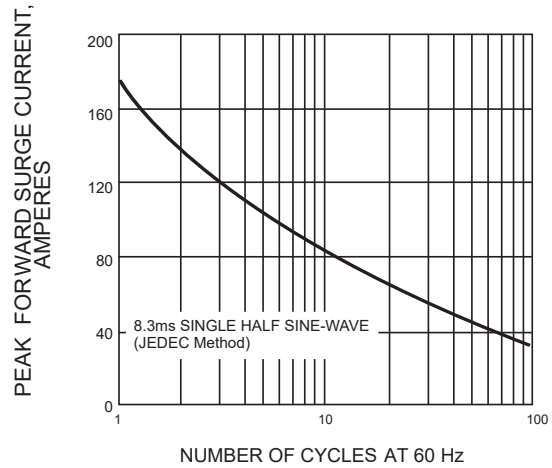


Fig.2 MAXIMUM NON-REPETITIVE SURGE CURRENT

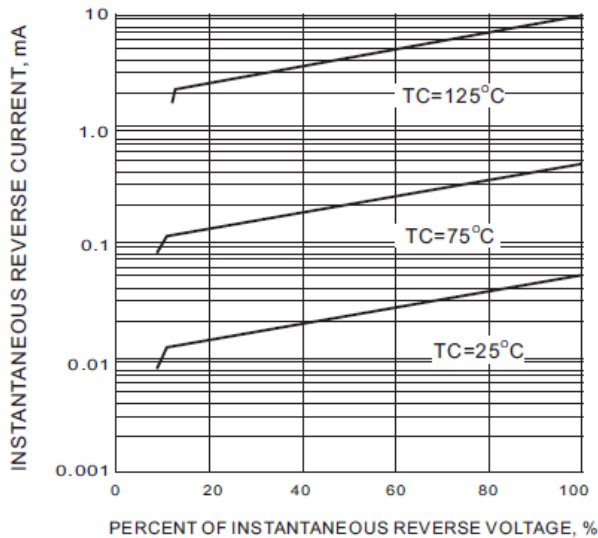


Fig.3 TYPICALREVERSE CHARACTERISTIC

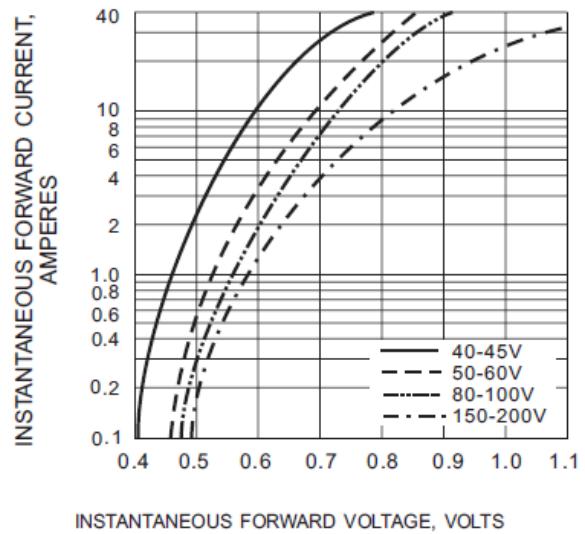
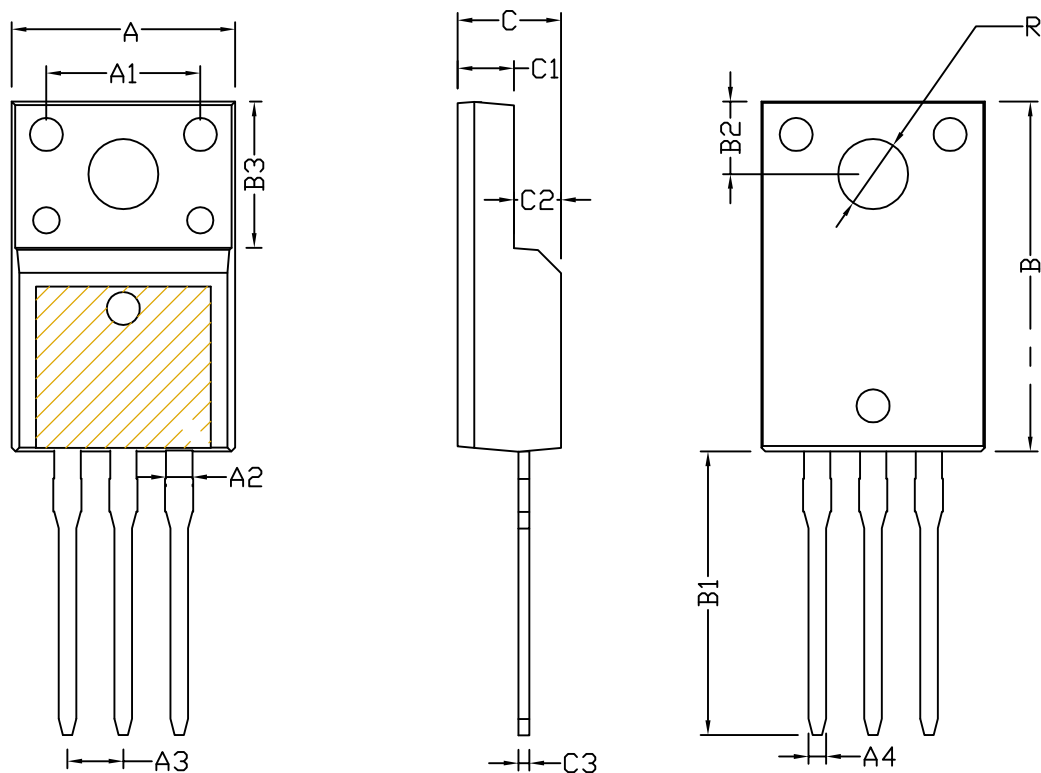


Fig.4 TYPICAL INSTANTANEOUS FORWARD CHARACTERISTIC



MBRF2040-MBRF20200
20 AMPS SCHOTTKY BARRIER RECTIFIER

Package Dimension



标注	最小	标准	最大	标注	最小	标准	最大	标注	最小	标准	最大
A	10.03	10.13	10.23	B	15.81	15.91	16.01	C	4.62	4.7	4.78
A1	6.5	7.0	7.5	B1	12.79	12.89	12.99	C1	2.5	2.55	2.6
A2	1.20	1.28	1.36	B2	3.0	3.3	3.6	C2	2.1	2.15	2.2
A3		2.54		B3	6.6	6.65	6.7	C3		0.5	
A4	0.7	0.8	0.9	R		3.18					